Takanori Kiguchi

List of Publications by Year in descending order

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257450 206112 2,762 169 24 citations h-index papers

48 g-index 176 176 176 2835 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Lower-temperature processing of potassium niobate films by microwave-assisted hydrothermal deposition technique. Journal of the Ceramic Society of Japan, 2022, 130, 123-130.	1.1	1
2	Metalloid substitution elevates simultaneously the strength and ductility of face-centered-cubic high-entropy alloys. Acta Materialia, 2022, 225, 117571.	7.9	64
3	Structural evolution of epitaxial CeO2-HfO2 thin films using atomic-scale observation: Formation of ferroelectric phase and domain structure. Acta Materialia, 2022, 235, 118091.	7.9	7
4	Electricâ€Fieldâ€Induced Ferroelectricity in 5%Yâ€doped Hf _{0.5} Zr _{0.5} O ₂ : Transformation from the Paraelectric Tetragonal Phase to the Ferroelectric Orthorhombic Phase. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2000589.	2.4	23
5	Electricâ€Fieldâ€Induced Ferroelectricity in 5%Yâ€doped Hf _{0.5} Zr _{0.5} O ₂ : Transformation from the Paraelectric Tetragonal Phase to the Ferroelectric Orthorhombic Phase. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2170023.	2.4	1
6	Effect of Ta substitution on the synthesis of (K,Na)(Nb,Ta)O ₃ powders by hydrothermal reaction: Insight into the combination of alkaline solution and raw powder. Journal of the Ceramic Society of Japan, 2021, 129, 365-371.	1.1	1
7	Ferroelectric and magnetic properties in <i>lμ</i> -Fe2O3 epitaxial film. Applied Physics Letters, 2021, 119, .	3.3	3
8	Good piezoelectricity of self-polarized thick epitaxial (K,Na)NbO3 films grown below the Curie temperature (240 °C) using a hydrothermal method. Applied Physics Letters, 2020, 117, .	3. 3	8
9	Enhanced intrinsic piezoelectric response in (001)-epitaxial single <i>c</i> -domain Pb(Zr,Ti)O3 nanorods. Applied Physics Letters, 2020, 117, .	3.3	3
10	Growth mechanism and domain structure study on epitaxial BiFeO3 film grown on (La0.3Sr0.7)(Al0.65Ta0.35)O3. Journal of Applied Physics, 2020, 127, .	2.5	5
11	Energy storage properties of epitaxially grown <i>x</i> CaZrO3–(1â^' <i>x</i>)NaNbO3 thin films prepared with chemical solution deposition method. Journal of Applied Physics, 2020, 128, .	2.5	5
12	Structural and electrical characterization of hydrothermally deposited piezoelectric (K,Na)(Nb,Ta)O3 thick films. Journal of Materials Science, 2020, 55, 8829-8842.	3.7	8
13	Strain self-accommodation during growth of 14H type long-period stacking ordered (LPSO) structures in Mg-Zn-Gd alloy. Scripta Materialia, 2020, 185, 25-29.	5.2	9
14	Impact of hydrochloric acid on the epitaxial growth of In ₂ O ₃ films on (0001) <i><math>\hat{l}\pm>-Al₂O₃ substrates by mist CVD. Applied Physics Express, 2020, 13, 075504.</math></i>	2.4	6
15	Epitaxial mist chemical vapor deposition growth and characterization of Cu3N films on (0001)α-Al2O3 substrates. Applied Physics Express, 2020, 13, 075505.	2.4	1
16	Redox-Based Multilevel Resistive Switching in AlFeO ₃ Thin-Film Heterostructures. ACS Applied Electronic Materials, 2020, 2, 1065-1073.	4.3	4
17	Enhanced photovoltaic effects in ferroelectric solid solution thin films with nanodomains. Applied Physics Letters, 2020, 116, .	3.3	17
18	Switchable third ScFeO ₃ polar ferromagnet with YMnO ₃ -type structure. Journal of Materials Chemistry C, 2020, 8, 4447-4452.	5 . 5	13

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19	High yield preparation of (100) <i>_c</i> -oriented (K,Na)NbO ₃ thick films by hydrothermal method using amorphous niobium source. Journal of the Ceramic Society of Japan, 2020, 128, 512-517.	1.1	9
20	Epitaxial growth mechanism of Pb(Zr,Ti)O ₃ thin films on SrTiO ₃ by chemical solution deposition via self-organized seed layer. Journal of the Ceramic Society of Japan, 2020, 128, 501-511.	1.1	4
21	Interface reaction between PbTiO ₃ epitaxial thin films and La-doped SrTiO ₃ (001) substrates through edge dislocations induced by 90° domain formation. Journal of the Ceramic Society of Japan, 2020, 128, 492-500.	1.1	2
22	Rapid deposition of (K,Na)NbO3 thick films using microwave-assisted hydrothermal technique. Japanese Journal of Applied Physics, 2020, 59, SPPB02.	1.5	7
23	Growth of (110)-one-axis-oriented perovskite-type oxide thin films with local epitaxy on (111)SrTiO3 single crystal substrates. Japanese Journal of Applied Physics, 2019, 58, SLLB01.	1.5	0
24	Influence of interfacial structure on propagating direction of small-angle grain boundaries during directional solidification of multicrystalline silicon. Scripta Materialia, 2019, 172, 105-109.	5.2	6
25	Interface structure of Pb(Zr,Ti)O3/MgO(001) epitaxial thin film in early stage of Stranski–Krastanov growth mode. Japanese Journal of Applied Physics, 2019, 58, SLLA08.	1.5	4
26	Effect of Ta-substitution on the deposition of (K,Na)(Nb,Ta)O3 films by hydrothermal method. Japanese Journal of Applied Physics, 2019, 58, SLLB12.	1.5	8
27	Growth of epitaxial (K, Na)NbO3 films with various orientations by hydrothermal method and their properties. Japanese Journal of Applied Physics, 2019, 58, SLLB14.	1.5	11
28	Effects of starting materials on the deposition behavior of hydrothermally synthesized {1 0 0} -oriented epitaxial (K,Na)NbO3 thick films and their ferroelectric and piezoelectric properties. Journal of Crystal Growth, 2019, 511, 1-7.	1.5	18
29	Short range biaxial strain relief mechanism within epitaxially grown BiFeO3. Scientific Reports, 2019, 9, 6715.	3.3	6
30	Formation of the orthorhombic phase in CeO2-HfO2 solid solution epitaxial thin films and their ferroelectric properties. Applied Physics Letters, 2019, 114 , .	3.3	30
31	Evaluation of spatial and temporal resolution on in situ annealing aberration-corrected transmission electron microscopy with proportional–integral–differential controller. Microscopy (Oxford,) Tj ETQq1 1 0.7	84 3.5 4 rgl	3T / Overlock
32	Effects of heat treatment and in situ high-temperature X-ray diffraction study on the formation of ferroelectric epitaxial Y-doped HfO ₂ film. Japanese Journal of Applied Physics, 2019, 58, SBBB09.	1.5	34
33	Deposition of orientation-controlled thick (K,Na)NbO ₃ films on metal substrates by repeated hydrothermal deposition technique. Journal of the Ceramic Society of Japan, 2019, 127, 478-484.	1.1	7
34	Low-temperature deposition of Li substituted (K,Na)NbO ₃ films by a hydrothermal method and their structural and ferroelectric properties. Journal of the Ceramic Society of Japan, 2019, 127, 388-393.	1.1	8
35	Misfit Strain Induced Interface Structure in PMN-PT Epitaxial Thin Films. Materia Japan, 2019, 58, 97-97.	0.1	O
36	Evolution of long-period stacking order (LPSO) in Mg97Zn1Gd2 cast alloys viewed by HAADF-STEM multi-scale electron tomography. Philosophical Magazine, 2018, 98, 1945-1960.	1.6	6

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37	Ferroelectric and Magnetic Properties in Roomâ€Temperature Multiferroic Ga <i>_x</i> Fe _{2â°} <i>_x</i> O ₃ Epitaxial Thin Films. Advanced Functional Materials, 2018, 28, 1704789.	14.9	44
38	On the atomic structure of γ″ phase in Mg-Zn-Gd alloy. Scripta Materialia, 2018, 146, 64-67.	5.2	37
39	Ferroelectricity mediated by ferroelastic domain switching in HfO2-based epitaxial thin films. Applied Physics Letters, 2018, 113, .	3.3	69
40	Formation of polar phase in Fe-doped ZrO2 epitaxial thin films. Applied Physics Letters, 2018, 113, .	3.3	8
41	Domain orientation relationship of orthorhombic and coexisting monoclinic phases of YO _{1.5} -doped HfO ₂ epitaxial thin films. Japanese Journal of Applied Physics, 2018, 57, 11UF16.	1.5	16
42	Fabrication of ferroelectric Fe doped HfO ₂ epitaxial thin films by ion-beam sputtering method and their characterization. Japanese Journal of Applied Physics, 2018, 57, 11UF02.	1.5	23
43	Preparation of {001} _c -oriented epitaxial (K, Na)NbO ₃ thick films by repeated hydrothermal deposition technique. Journal of the Ceramic Society of Japan, 2018, 126, 281-285.	1.1	10
44	Creation of Ferroelectric Thin Films with Nanosize Domain Structure. Hosokawa Powder Technology Foundation ANNUAL REPORT, 2018, 26, 66-72.	0.0	0
45	Effect of the film thickness on the crystal structure and ferroelectric properties of (Hf 0.5 Zr 0.5)O 2 thin films deposited on various substrates. Materials Science in Semiconductor Processing, 2017, 70, 239-245.	4.0	41
46	Crystal structure and magnetism in \hat{l}^2 -Al2O3-type AlxFe2-xO3 films on SrTiO3(111). Journal of Applied Physics, 2017, 122, 015301.	2.5	14
47	Strain-induced nanostructure of Pb(Mg _{1/3} Nb _{2/3})O ₃ â€"PbTiO ₃ on SrTiO ₃ epitaxial thin films with low PbTiO ₃ concentration. Japanese Journal of Applied Physics, 2017, 56, 10PB12.	1.5	8
48	Characterization of (111)-oriented epitaxial (K _{0.5} Na _{0.5})NbO ₃ thick films deposited by hydrothermal method. Japanese Journal of Applied Physics, 2017, 56, 10PF04.	1.5	10
49	Polarization switching behavior of one-axis-oriented lead zirconate titanate films fabricated on metal oxide nanosheet layer. Japanese Journal of Applied Physics, 2017, 56, 10PF10.	1.5	2
50	Three-Dimensional Imaging of a Long-Period Stacking Ordered Phase in Mg ₉₇ Zn ₁ Gd ₂ Using High-Voltage Electron Microscopy. Materials Transactions, 2016, 57, 918-921.	1.2	3
51	Bulk and domain-wall effects in ferroelectric photovoltaics. Physical Review B, 2016, 94, .	3.2	43
52	Thermally stable dielectric responses in uniaxially (001)-oriented CaBi4Ti4O15 nanofilms grown on a Ca2Nb3O10â ⁻² nanosheet seed layer. Scientific Reports, 2016, 6, 20713.	3.3	8
53	Impact of mechanical stress on ferroelectricity in (Hf0.5Zr0.5)O2 thin films. Applied Physics Letters, 2016, 108, .	3.3	187
54	Crystal structure and compositional analysis of epitaxial (K _{0.56} Na _{0.44} NbO ₃ films prepared by hydrothermal method. Journal of Materials Research, 2016, 31, 693-701.	2.6	7

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55	Growth of (111)-oriented epitaxial and textured ferroelectric Y-doped HfO2 films for downscaled devices. Applied Physics Letters, 2016, 109, .	3.3	62
56	Orientation control and domain structure analysis of $\{100\}$ -oriented epitaxial ferroelectric orthorhombic HfO2-based thin films. Journal of Applied Physics, 2016, 119, .	2.5	57
57	Formation of (111) orientation-controlled ferroelectric orthorhombic HfO2 thin films from solid phase via annealing. Applied Physics Letters, 2016, 109, .	3.3	29
58	Fabrication and characterization of (111)-epitaxial Pb(Zr0.35Ti0.65)O3/Pb(Zr0.65Ti0.35)O3artificial superlattice thin films. Japanese Journal of Applied Physics, 2016, 55, 10TA20.	1.5	2
59	Atomic-resolution analysis for the effects of heat treatment temperatures on the growth of chemically-ordered regions in Pb(Mg _{1/3} Nb _{2/3})O ₃ thin films. Journal of the Ceramic Society of Japan, 2016, 124, 697-701.	1.1	3
60	Solid state epitaxy of (Hf,Zr)O ₂ thin films with orthorhombic phase. Journal of the Ceramic Society of Japan, 2016, 124, 689-693.	1.1	34
61	The demonstration of significant ferroelectricity in epitaxial Y-doped HfO2 film. Scientific Reports, 2016, 6, 32931.	3.3	194
62	Orientation control of barium titanate films using metal oxide nanosheet layer. Japanese Journal of Applied Physics, 2016, 55, 10TA15.	1.5	5
63	Magnetic-field-induced spontaneous superlattice formation via spinodal decomposition in epitaxial strontium titanate thin films. NPG Asia Materials, 2016, 8, e279-e279.	7.9	19
64	Texture Observation for α-Fe ₂ O ₃ Doped HfO ₂ Ultrathin Films. Materia Japan, 2016, 55, 599-599.	0.1	0
65	Fabrication of (100) _c -oriented Mn-doped bismuth ferrite films on silicon and stainless steel substrates using calcium niobate nanosheets. Journal of the Ceramic Society of Japan, 2015, 123, 322-328.	1.1	5
66	Effect of Ti concentration on the growth of chemically-ordered regions of Pb(Mg _{1/3} Nb _{2/3})O ₃ –PbTiO&lepitaxial thin films. Journal of the Ceramic Society of Japan, 2015, 123, 565-569.	t;s ub >3	&l z ;/sub>
67	Three-Dimensional Shapes and Distributions of Long-Period Stacking Ordered Structures in Mg ₉₇ Zn ₁ Gd ₂ Cast Alloys Characterized by Electron Tomography. Materials Transactions, 2015, 56, 928-932.	1.2	6
68	Effect of Focal Depth of HAADF-STEM Imaging on the Solute Enriched Layers in Mg Alloys. Materials Transactions, 2015, 56, 1633-1638.	1.2	12
69	Local Strain Fields of LPSO in Mg-Based Ternary Alloys. Materials Transactions, 2015, 56, 923-927.	1.2	7
70	Negligible substrate clamping effect on piezoelectric response in (111) -epitaxial tetragonal Pb(Zr, Ti)O3 films. Journal of Applied Physics, 2015, 118, .	2.5	21
71	Contribution of oxygen vacancies to the ferroelectric behavior of Hf0.5Zr0.5O2 thin films. Applied Physics Letters, 2015, 106, .	3.3	65
72	Growth of epitaxial orthorhombic YO1.5-substituted HfO2 thin film. Applied Physics Letters, 2015, 107, .	3.3	123

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73	Polar-axis-oriented crystal growth of tetragonal PZT films on stainless steel substrate using pseudo-perovskite nanosheet buffer layer. AIP Advances, 2015, 5, .	1.3	6
74	Control of geometry in Si-based photonic nanostructures formed by maskless wet etching process and its impact on optical properties. Thin Solid Films, 2014, 557, 338-341.	1.8	9
75	Carrier extraction dynamics from Ge/Si quantum wells in Si solar cells. Thin Solid Films, 2014, 557, 368-371.	1.8	10
76	Compositional Transition Layer around Growing LPSO in Mg ₉₇ Zn ₁ Y ₂ Cast Alloys. Materials Transactions, 2014, 55, 1377-1382.	1.2	3
77	Dielectric property of (001) one-axis oriented CaBi ₄ Ti ₄ O ₁₅ -based thin films and their temperature dependence. Journal of the Ceramic Society of Japan, 2014, 122, 477-482.	1.1	2
78	Columnar grain boundary coherence in yttria-stabilized zirconia thin film: effects on ionic conductivity. Journal of the Ceramic Society of Japan, 2014, 122, 72-77.	1.1	12
79	Chemical and structural effects on ionic conductivity at columnar grain boundaries in yttria-stabilized zirconia thin films. Journal of the Ceramic Society of Japan, 2014, 122, 430-435.	1.1	2
80	Effect of Ge/Si heterostructures on carrier extraction in Si solar cells with Ge quantum dots. , 2013, , .		0
81	TEM Analysis of the Nanostructure of Pb(Mg _{1/3} Nb _{2/3})O ₃ Thin Films by MOD Method. Key Engineering Materials, 2013, 582, 19-22.	0.4	2
82	Direct Observation of Atomic Arrangement around $90\hat{A}^\circ$ Domain Wall in Lead Titanate Thin Films Materials Research Society Symposia Proceedings, 2013, 1515, 1.	0.1	1
83	Control of Dip Shape in Photonic Nanostructures by Maskless Wet-Etching Process and Its Impact on Optical Properties. Japanese Journal of Applied Physics, 2013, 52, 080202.	1.5	7
84	Nano-Structure around $90\hat{A}^\circ$ Domain Wall and Elastic Interaction with Misfit Dislocation in PbTiO ₃ Thin Film. Key Engineering Materials, 2013, 566, 167-170.	0.4	1
85	Crystal Structure Analysis of Hydrothermally Synthesized Epitaxial (K _x Na _{1-x})NbO ₃ Films. Japanese Journal of Applied Physics, 2013, 52, 09KA11.	1.5	22
86	Growth of vertical silicon nanowires array using electrochemical alternative. , 2013, , .		2
87	Nanostructure and Strain Field in Vertically Aligned Nano-Islands for Si/Ge 2D Photonic Nanocrystals Materials Research Society Symposia Proceedings, 2013, 1510, 1.	0.1	2
88	Stress state analysis of stress engineered BaTiO ₃ thin film by LaNiO ₃ bottom electrode. Journal of the Ceramic Society of Japan, 2013, 121, 273-277.	1.1	0
89	Effect of facing annealing on crystallization and decomposition of Pb(Mg _{1/3} Nb _{2/3})O ₃ thin films prepared by CSD technique using MOD solution. Journal of the Ceramic Society of Japan, 2013, 121, 236-241.	1.1	12
90	Effect of facing annealing on crystallization and decomposition of Pb(Mg _{1/3} Nb _{2/3})O ₃ thin films prepared by CSD technique using MOD solution. Journal of the Ceramic Society of Japan, 2013, 121, 326-326.	1.1	0

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91	Micro/Crystal structure analysis of CSD derived porous LaNiO ₃ electrode films. Journal of the Ceramic Society of Japan, 2013, 121, 619-622.	1.1	4
92	Effect of excess Pb on epitaxial growth of Pb(Mg _{1/3} thin films prepared by chemical solution deposition process. Journal of the Ceramic Society of Japan, 2013, 121, 638-643.	1.1	5
93	Fabrication and electrochemical performance of lithium polymer battery using mesoporous silica/polymer hybrid electrolyte. Journal of the Ceramic Society of Japan, 2013, 121, 723-729.	1.1	5
94	Structural and Compositional Modulation in Transformation of LPSO Structure in Mg ₉₇ Zn ₁ Y ₂ Cast Alloys. Materials Transactions, 2013, 54, 668-674.	1,2	35
95	Fabrication and Evaluation of One-Axis Oriented Lead Zirconate Titanate Films Using Metal–Oxide Nanosheet Interface Layer. Japanese Journal of Applied Physics, 2013, 52, 09KA04.	1.5	11
96	TEM MICROSTRUCTURE ANALYSIS FOR COMPRESSIVELY STRESSED Pb(Zr,Ti)O₃ THIN FILMS BY CSD-DERIVED LaNiO₃ BOTTOM ELECTRODES. Functional Materials Letters, 2012, 05, 1260016.	1.2	3
97	Molecular Dynamics Simulation of 90° Ferroelectric Domains in PbTiO ₃ . Journal of the Physical Society of Japan, 2012, 81, 124702.	1.6	17
98	Low temperature processing of alkoxide-derived PMN thin films. IOP Conference Series: Materials Science and Engineering, 2012, 30, 012002.	0.6	3
99	Simultaneous enhanced photon capture and carrier generation in Si solar cells using Ge quantum dot photonic nanocrystals. Nanotechnology, 2012, 23, 185401.	2.6	36
100	Stacking faults in an epitaxially grown PbTiO3 thick film and their size distribution. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2012, 177, 528-531.	3.5	1
101	TEM Observation on Ferroelectric Domain Structures of PbTiO ₃ Epitaxial Films. Key Engineering Materials, 2011, 485, 179-182.	0.4	0
102	Fabrication of Ferromagnetic Ni(111) Nanoparticles Embedded Epitaxially in (Mg,Ni)O Matrix by Reduction of (Mg0.5Ni0.5)O(111) Epitaxial Thin Film. Japanese Journal of Applied Physics, 2011, 50, 070206.	1.5	1
103	Configuration and local elastic interaction of ferroelectric domains and misfit dislocation in PbTiO ₃ /SrTiO ₃ epitaxial thin films. Science and Technology of Advanced Materials, 2011, 12, 034413.	6.1	41
104	Diffraction contrast analysis of 90° and 180° ferroelectric domain structures of PbTiO ₃ thin films. Science and Technology of Advanced Materials, 2011, 12, 034403.	6.1	14
105	Nanostructure and strain analysis of CeO2/YSZ strained superlattice. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 220-228.	3.5	2
106	Antiferrodistortive Structural Phase Transition in Compressively-Strained Epitaxial SrTiO3 Film Grown on (La, Sr)(Al, Ta)O3 Substrate. Integrated Ferroelectrics, 2010, 115, 57-62.	0.7	6
107	Crystal Structure and Dielectric Property of Bismuth Layer-Structured Dielectric Films withc-Axis Preferential Crystal Orientation. Japanese Journal of Applied Physics, 2010, 49, 09MA02.	1.5	16
108	Good Conformability of Indium-Tin Oxide Thin Films Prepared by Spray Chemical Vapor Deposition. Electrochemical and Solid-State Letters, 2009, 12, D42.	2.2	7

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109	Geometric Phase Analysis of Nano-Scale Strain Fields Around 90° Domains in PbTiO3/SrTiO3 Epitaxial Thin Film. Materials Research Society Symposia Proceedings, 2009, 1199, 12.	0.1	2
110	Electronic structure analyses of the interface between a high refractive index optical glass and carbides. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 161, 20-26.	3 . 5	0
111	Valence-EELS analysis of local electronic and optical properties of PMN–PT epitaxial film. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 161, 160-165.	3.5	17
112	Ferroelectric Properties of Epitaxial BiFe _{0.9} 7Mn _{0.03} O ₃ Thin Films with Different Crystal Orientations Deposited on Buffered Si Substrates. Key Engineering Materials, 2009, 421-422, 111-114.	0.4	0
113	Doping effect of Dy on leakage current and oxygen sensing property of SrTiO3 thin film prepared by PLD. Journal of the Ceramic Society of Japan, 2009, 117, 1004-1008.	1.1	3
114	Epitaxial growth of winding ZnO nanowires on a single-crystalline substrate. Journal of the Ceramic Society of Japan, 2009, 117, 255-257.	1.1	4
115	Transition Layer in ZrO2 Ultra-Thin Film by Aberration-corrected TEM. Materia Japan, 2009, 48, 599-599.	0.1	0
116	Ruddlesdenâ€Popperâ€Type Epitaxial Film as Oxygen Electrode for Solidâ€Oxide Fuel Cells. Advanced Materials, 2008, 20, 4124-4128.	21.0	55
117	Advantage of the structure and the electrical properties of epitaxial ultra-thin zirconia gate dielectrics. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 148, 30-34.	3 . 5	7
118	Step coverage study of indium-tin-oxide thin films by spray CVD on non-flat substrates at different temperatures. Thin Solid Films, 2008, 516, 5864-5867.	1.8	23
119	Effect of SrTiO3 seed layer deposition time and thickness on low-temperature crystallization and electrical properties of Pb(Zr, Ti)O3 films by metalorganic chemical vapor deposition. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 148, 22-25.	3.5	7
120	Fabrication and optical properties of Pb(Mg _{1/3} Nb _{2/3})O ₃ -PbTiO ₃ thin films on Si substrates using the PLD method. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2008, 55, 1023-1028.	3.0	15
121	Preparation of Epitaxial Pt Bottom Electrode and Tunability of (Ba,Sr)TiO ₃ Thin Film Deposited on Si Substrate. Ferroelectrics, 2008, 370, 132-139.	0.6	O
122	Preparation and Structure of Lead Magnesium Niobate Titanate Film by Double-Pulse Excitation using Nd:YAG and KrF Excimer Lasers. Japanese Journal of Applied Physics, 2007, 46, 657-659.	1.5	7
123	Fabrication and Optical Properties of Pb(Mg <inf>1/3</inf> Nb <inf>2/3</inf>)O <inf>3</inf> PbTiO <inf>3</inf> Thin Films on Si Substrates by PLD Method. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	0
124	Effect of Source Supply Methods on Low-Temperature Preparation of Lead Zirconate Titanate Thin Films Using SrTiO ₃ Seed Layers by Metallorganic Chemical Vapor Deposition. Solid State Phenomena, 2007, 124-126, 153-156.	0.3	3
125	Fabrication and Microstructural Change of PMN-PT Thin Films on Si Substrates by PLD with Mask and Double-Pulse Lazer Excitation. Key Engineering Materials, 2007, 350, 111-114.	0.4	6
126	Solution-Based Fabrication of High-κ Dielectric Nanofilms Using Titania Nanosheets as a Building Block. Japanese Journal of Applied Physics, 2007, 46, 6979.	1.5	9

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127	Preparation of ferromagnetic zinc-ferrite thin film by pulsed laser deposition in the magnetic field. Journal of Magnetism and Magnetic Materials, 2007, 310, 2546-2548.	2.3	58
128	Room-Temperature Electrical-Field Induced Oxygen Diffusion of Aluminum/Yttria-Stabilized Zirconia Thin Film Grown on Si Substrate. Japanese Journal of Applied Physics, 2006, 45, 8827-8831.	1.5	2
129	Atomic-Scale Structure Investigation of CeO ₂ /YSZ/Si Hetero-Interface by High Resolution Analytical Electron Microscope. Bunseki Kagaku, 2006, 55, 419-426.	0.2	0
130	High-κ Dielectric Nanofilms Fabricated from Titania Nanosheets. Advanced Materials, 2006, 18, 1023-1027.	21.0	206
131	Activation Energy of Oxygen Vacancy Diffusion of Yttria-Stabilized-Zirconia Thin Film Determined from DC Current Measurements below 150 °C. Japanese Journal of Applied Physics, 2006, 45, L525-L528.	1.5	6
132	Preparation and Optical Properties of Epitaxial Pb(Mg _{1/3} Nb _{2/3} 3-PbTiO _{3< Thin Film on Si Substrates with Buffer Layer Using Pulsed Laser Deposition. Key Engineering Materials, 2006, 301, 265-268.}	/sub> 0.4	6
133	Crystal Growth of β-FeSi2 Thin Film on (100), (110) and (111) Plane of Si and Yittria-stabilized Zirconia Substrates. Materials Research Society Symposia Proceedings, 2006, 980, 47.	0.1	0
134	In-Plane and Out-of-Plane Ferroelectric Instabilities in EpitaxialSrTiO3Films. Physical Review Letters, 2006, 96, 157602.	7.8	30
135	Enhanced piezoelectric properties of barium titanate single crystals with different engineered-domain sizes. Journal of Applied Physics, 2005, 98, 014109.	2.5	319
136	High-temperature in situ Cross-sectional Transmission Electron Microscopy Investigation of Crystallization Process of Yttrium-stabilized Zirconia/Si and Yttrium-stabilized Zirconia/SiOx/Si Thin Films. Journal of Materials Research, 2005, 20, 1878-1887.	2.6	5
137	Epitaxial Growth of CeO ₂ , Thin Film on Si (001) Wafer Using YSZ Seeding Layer. Materia Japan, 2004, 43, 988-988.	0.1	0
138	AEM Investigation of Interface Structure of Y ₂ O ₃ -Ta ₂ O ₅ Co-Doped Zirconia Buffer Layer. Key Engineering Materials, 2004, 269, 237-240.	0.4	3
139	Effect of deposition temperature on the characteristics of hafnium oxide films deposited by metalorganic chemical vapor deposition using amide precursor. Journal of Materials Research, 2004, 19, 584-589.	2.6	11
140	IN-SITU TEM INVESTIGATION OF STRUCTURAL CHANGES IN ZIRCONIA/SILICON HETEROSTRUCTURES AT ELEVATED TEMPERATURE. International Journal of Nanoscience, 2004, 03, 699-705.	0.7	1
141	Characterization of defect type and dislocation density in double oxide heteroepitaxial CeO 2 /YSZ/Si(001) films. Applied Physics A: Materials Science and Processing, 2003, 76, 969-973.	2.3	13
142	HRTEM investigation of the $90\hat{A}^\circ$ domain structure and ferroelectric properties of multi-layered PZT thin films. Microelectronic Engineering, 2003, 66, 708-712.	2.4	10
143	Improvement of C-V Characteristics and Control of Interlayer Growth of Rare Earth Oxide Stabilized Zirconia Epitaxial Gate Dielectrics. Key Engineering Materials, 2003, 248, 137-142.	0.4	6
144	Role of Ultra Thin SiOx Layer on Epitaxial YSZ/SiOx/Si Thin Film. Integrated Ferroelectrics, 2003, 51, 51-61.	0.7	7

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TAKANORI KIGUCHI

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